

**Amendments to the Specification:**

On page 7, line 1 of the specification, before the first full paragraph, please insert the following new paragraph:

C1 -- Figure 14 A is a cross-sectional view of a representative silicon structure according to a third embodiment of the present invention and at a stage of processing subsequent to that shown in Figure 4. --

On page 18, line 14, please amend the paragraph, which extends to the top of page 19, as follows:

C2 Although the buried silicon structure 100 is shown in Figure 14 as comprising only three buried conductor patterns 70, 80, and 90, respectively, it must be readily apparent to those skilled in the art that in fact any number of such buried conductor patterns may be formed ~~on~~ in the substrate 10, as pipes, plates, or spheres, by methods of the present invention. Also, although the exemplary embodiments described above refer to the formation of buried conductor patterns having specific shapes, it must be understood that other shapes, configurations or geometries may be employed, depending on the characteristics of the particular IC device to be fabricated. For example, as shown in Figure 14A, a buried silicon structure 101 may comprise three buried conductor patterns 71, 81, and 91, which may be pipe-shaped, sphere-shaped, and plate-shaped, respectively. Further, the invention is not limited to a combination of three buried conductor patterns, but any combination of any number of empty-spaced patterns filled with a conductor may be employed, as desired.